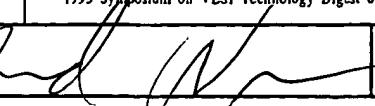
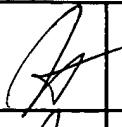
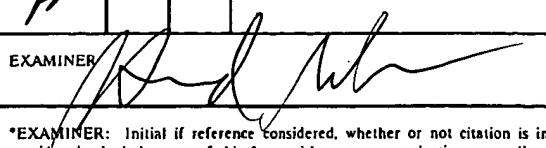


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					FILING DATE Filed Herewith	GROUP		
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,045,899	09/03/91	Arimoto				
	AB	5,107,459	04/21/92	Chu et al.				
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	AK	5,665,623	09/09/97	Liang et al.				
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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL	JP 03205868	09/09/91	Japan			Abs.	
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
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EXAMINER			DATE CONSIDERED					
<i>[Signature]</i>			9/17/04					
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								

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*Examiner Initial		Document Number	Date	Name	Class Subclass Filing Date If Appropriate		
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		Document Number	Date	Country	Class Subclass	Translation	
						Yes	No
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	AL						
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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	AQ						
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